

## N-Channel Enhancement-Mode Vertical DMOS FET

#### **Features**

- Low threshold
- High input impedance
- Low input capacitance
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage
- Complementary N- and P-channel devices

#### **Applications**

- Logic level interfaces ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

#### **General Description**

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

#### **Ordering Information**

Part Number	Package Option	Packing
TN5335K1-G	TO-236AB (SOT-23)	3000/Reel
TN5335N8-G	TO-243AA (SOT-89)	2000/Reel

-G denotes a lead (Pb)-free / RoHS compliant package. Contact factory for Wafer / Die availablity. Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

### **Absolute Maximum Ratings**

	•
Parameter	Value
Drain-to-source voltage	BV <sub>DSS</sub>
Drain-to-gate voltage	$BV_{DGS}$
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

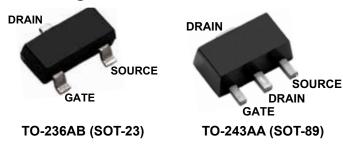
### **Typical Thermal Resistance**

Package	$oldsymbol{ heta}_{ja}$
TO-236AB (SOT-23)	203°C/W
TO-243AA (SOT-89)	173°C/W

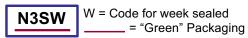
#### **Product Summary**

BV <sub>DSS</sub> /BV <sub>DGS</sub>	R <sub>DS(ON)</sub> (max)	l <sub>D(ON)</sub> (min)	V <sub>GS(th)</sub> (max)
350V	15Ω	750mA	2.0V

### **Pin Configuration**



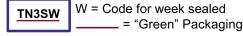
#### **Product Marking**



Package may or may not include the following marks: Si or 🌎

TO-236AB (SOT-23)

W = Code for week sealed



Package may or may not include the following marks: Si or 4

TO-243AA (SOT-89)

### **Thermal Characteristics**

Package	Ι <sub>D</sub> (continuous) <sup>†</sup>	I <sub>D</sub> (pulsed)	Power Dissipation @T <sub>A</sub> = 25°C	l <sub>DR</sub> †	DRM
TO-236AB (SOT-23)	110mA	0.8A	0.36W	110mA	0.8A
TO-243AA (SOT-89)	230mA	1.3A	1.6W <sup>‡</sup>	230mA	1.3A

#### Notes:

- †  $I_{D}$  (continuous) is limited by max rated  $T_{i}$ .
- # Mounted on FR5 Board, 25mm x 25mm x 1.57mm.

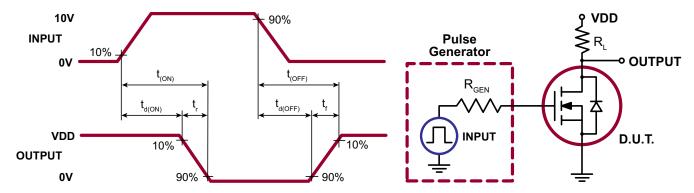
### Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions
BV <sub>DSS</sub>	Drain-to-source breakdown voltage	350	-	-	V	$V_{GS} = 0V, I_{D} = 100 \mu A$
$V_{\rm GS(th)}$	Gate threshold voltage	0.6	-	2.0	V	$V_{GS} = V_{DS}$ , $I_D = 1.0 \text{mA}$
$\Delta V_{GS(th)}$	Change in V <sub>GS(th)</sub> with temperature	-	-	-4.5	mV/°C	$V_{GS} = V_{DS}$ , $I_D = 1.0 \text{mA}$
I <sub>GSS</sub>	Gate body leakage	-	-	100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
		_	-	1.0		$V_{GS} = 0V$ , $V_{DS} = 100V$
	Zero gate voltage drain current	_	-	10	μA	$V_{GS} = 0V, V_{DS} = Max Rating$
DSS	Zoro gate voltage drain carrent	-	-	1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$ , $T_{A} = 125$ °C
	On state design surrent	300	-	-	A	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 25V
D(ON)	On-state drain current	750	-	-	mA	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 25V
			-	15		$V_{GS} = 3.0V, I_{D} = 20mA$
R <sub>DS(ON)</sub>	Static drain-to-source on-state resistance	-	-	15	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 150mA
		15 V <sub>GS</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 200mA			
$\Delta R_{DS(ON)}$	Change in R <sub>DS(ON)</sub> with temperature	-	-	1.0	%/°C	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 150mA
G <sub>FS</sub>	Forward transductance	125	-	-	mmho	$V_{DS} = 25V, I_{D} = 200mA$
C <sub>ISS</sub>	Input capacitance	-	-	110		V <sub>GS</sub> = 0V,
C <sub>oss</sub>	Common source output capacitance	-	-	60	pF	$V_{DS} = 25V$ ,
C <sub>RSS</sub>	Reverse transfer capacitance	-	-	22		f = 1.0MHz
t <sub>d(ON)</sub>	Turn-on delay time	-	-	20		
t <sub>r</sub>	Rise time		-	15	no	$V_{DD} = 25V,$
t <sub>d(OFF)</sub>	Turn-off delay time	-	-	25	ns	$I_D = 150 \text{mA},$ $R_{GEN} = 25\Omega$
t <sub>f</sub>	Fall time		-	25		SLI1
V <sub>SD</sub>	Diode forward voltage drop	-	-	1.8	V	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 200mA
t <sub>rr</sub>	Reverse recovery time	-	800	-	ns	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 200mA

#### Notes:

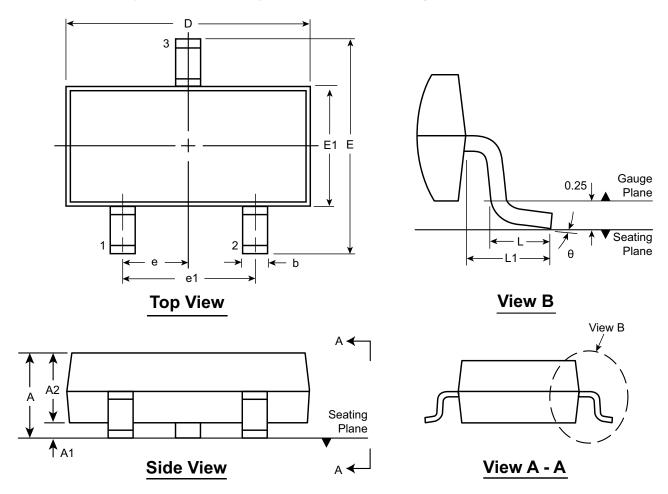
- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
   All A.C. parameters sample tested.

# **Switching Waveforms and Test Circuit**



# 3-Lead TO-236AB (SOT-23) Package Outline (K1)

## 2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



Symb	ol	Α	A1	A2	b	D	E	E1	е	e1	L	L1	θ		
<b>.</b> .	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.05	4.00	4.00	4.00	0.20†	0.54	<b>0</b> °
Dimension (mm)	NOM	-	-	0.95	-	2.90	-	1.30	0.95 BSC	1.90 BSC	0.50	0.54 REF	-		
(11111)	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40	В	ВОС	0.60	IVEI	<b>8</b> º		

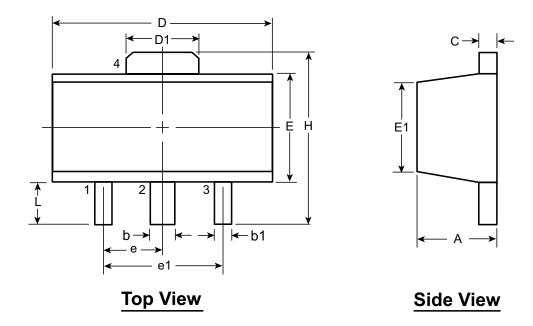
JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

† This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

## 3-Lead TO-243AA (SOT-89) Package Outline (N8)



Symbo	ol	Α	b	b1	С	D	D1	E	E1	е	e1	Н	L
	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.00 <sup>†</sup>			3.94	0.73 <sup>†</sup>
Dimensions (mm)	NOM	-	-	-	-	-	-	-	-	1.50 BSC	3.00 BSC	-	-
()	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29		200	4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

† This dimension differs from the JEDEC drawing

Drawings not to scale.

Supertex Doc. #: DSPD-3TO243AAN8, Version F111010.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <a href="http://www.supertex.com/packaging.html">http://www.supertex.com/packaging.html</a>.)

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